International IOR Rectifier

Data Sheet No. PD60162 Rev. W

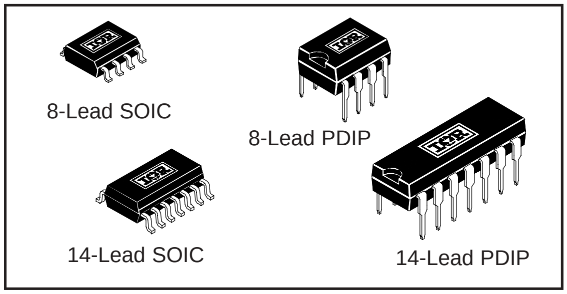
IR2106(4)(S) & (PbF)

HIGH AND LOW SIDE DRIVER

Features

- Floating channel designed for bootstrap operation
  Fully operational to +600V
  Tolerant to negative transient voltage
  dV/dt immune
- Gate drive supply range from 10 to 20V (IR2106(4))
- Undervoltage lockout for both channels
- 3.3V, 5V and 15V input logic compatible
- Matched propagation delay for both channels
- Logic and power ground +/- 5V offset.
- Lower di/dt gate driver for better noise immunity
- Outputs in phase with inputs (IR2106)
- Also available LEAD-FREE

Packages



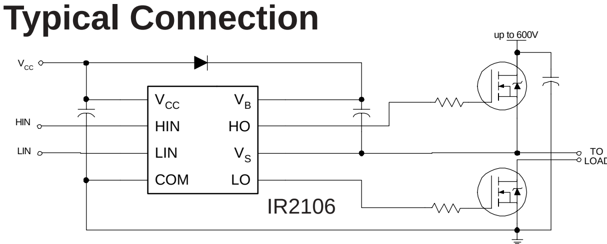
Description

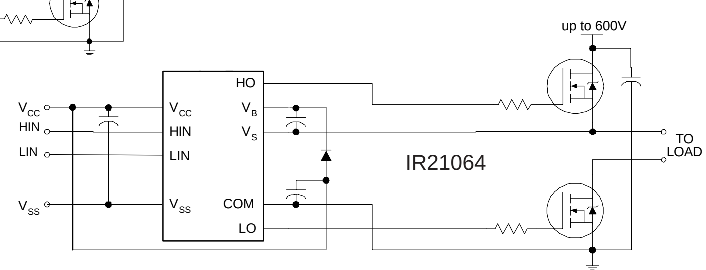
The IR2106(4)(S) are high voltage, high speed power MOSFET and IGBT drivers with independent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

2106/2301//2108//2109/2302/2304Feature Comparison

Part	Input logic	Cross-conduction prevention logic	Dead-Time	Ground Pins	Ton/Toff
2106/2301	HIN/LIN	no	none	COM	220/200
21064				VSS/COM	
2108	HIN/$\overline{LIN}$	yes	Internal 540ns	COM	220/200
21084			Programmable 0.54~5µs	VSS/COM	
2109/2302	IN/$\overline{SD}$	yes	Internal 540ns	COM	750/200
21094			Programmable 0.54~5µs	VSS/COM	
2304	HIN/LIN	yes	Internal 100ns	COM	160/140

Typical Connection





(Refer to Lead Assignments for correct pin configuration). This/These diagram(s) show electrical connections only. Please refer to our Application Notes and DesignTips for proper circuit board layout.

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition		Min.	Max.	Units
V_B	High side floating absolute voltage		-0.3	625	V
V_S	High side floating supply offset voltage		V_B - 25	V_B + 0.3	
V_{HO}	High side floating output voltage		V_S - 0.3	V_B + 0.3	
V_{CC}	Low side and logic fixed supply voltage		-0.3	25	
V_{LO}	Low side output voltage		-0.3	V_{CC} + 0.3	
V_{IN}	Logic input voltage		V_{SS} - 0.3	V_{CC} + 0.3	
V_{SS}	Logic ground (IR21064 only)		V_{CC} - 25	V_{CC} + 0.3	
dV_S/dt	Allowable offset supply voltage transient		—	50	V/ns
P_D	Package power dissipation @ $T_A \le +25°C$	(8 lead PDIP)	—	1.0	W
		(8 lead SOIC)	—	0.625	
		(14 lead PDIP)	—	1.6	
		(14 lead SOIC)	—	1.0	
Rth_{JA}	Thermal resistance, junction to ambient	(8 lead PDIP)	—	125	°C/W
		(8 lead SOIC)	—	200	
		(14 lead PDIP)	—	75	
		(14 lead SOIC)	—	120	
T_J	Junction temperature		—	150	°C
T_S	Storage temperature		-50	150	
T_L	Lead temperature (soldering, 10 seconds)		—	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S and V_{SS} offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage IR2106(4)	V_S + 10	V_S + 20	V
V_S	High side floating supply offset voltage	Note 1	600	
V_{HO}	High side floating output voltage	V_S	V_B	
V_{CC}	Low side and logic fixed supply voltage IR2106(4)	10	20	
V_{LO}	Low side output voltage	0	V_{CC}	
V_{IN}	Logic input voltage	V_{SS}	V_{CC}	
V_{SS}	Logic ground (IR21064 only)	-5	5	
T_A	Ambient temperature	-40	125	°C

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to $-V_{BS}$. (Please refer to the Design Tip DT97-3 for more details).

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15V, V_{SS} = COM, C_L = 1000 pF, T_A = 25°C.

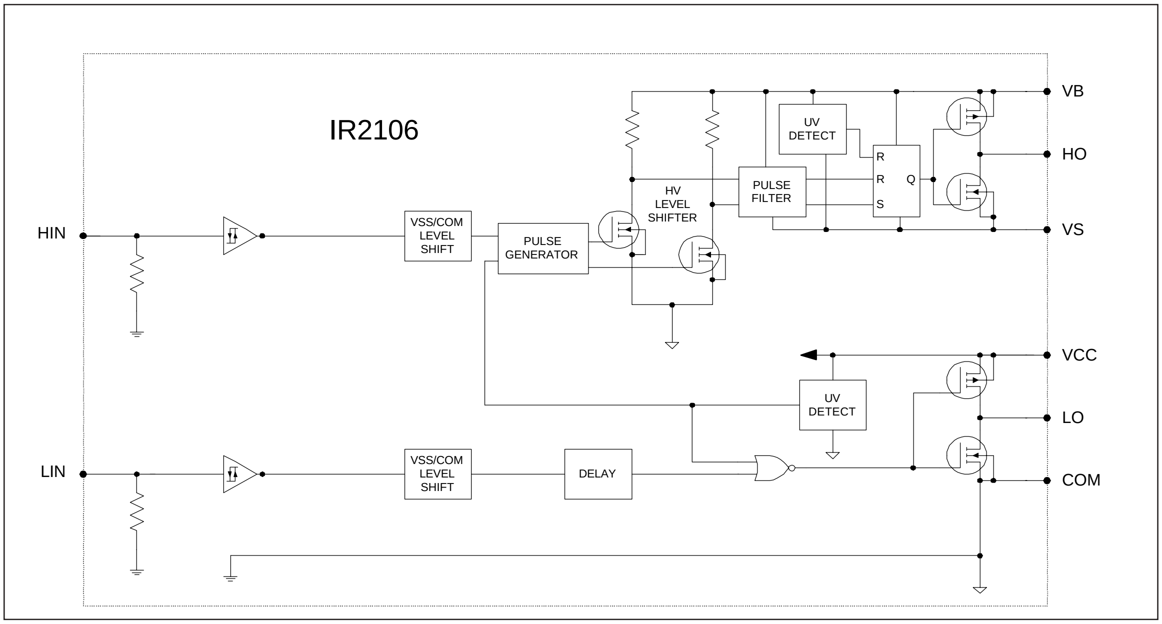
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
t_{on}	Turn-on propagation delay	—	220	300	nsec	V_S = 0V
t_{off}	Turn-off propagation delay	—	200	280		V_S = 0V or 600V
MT	Delay matching, HS & LS turn-on/off	—	0	30		
t_r	Turn-on rise time	—	150	220		V_S = 0V
t_f	Turn-off fall time	—	50	80		V_S = 0V

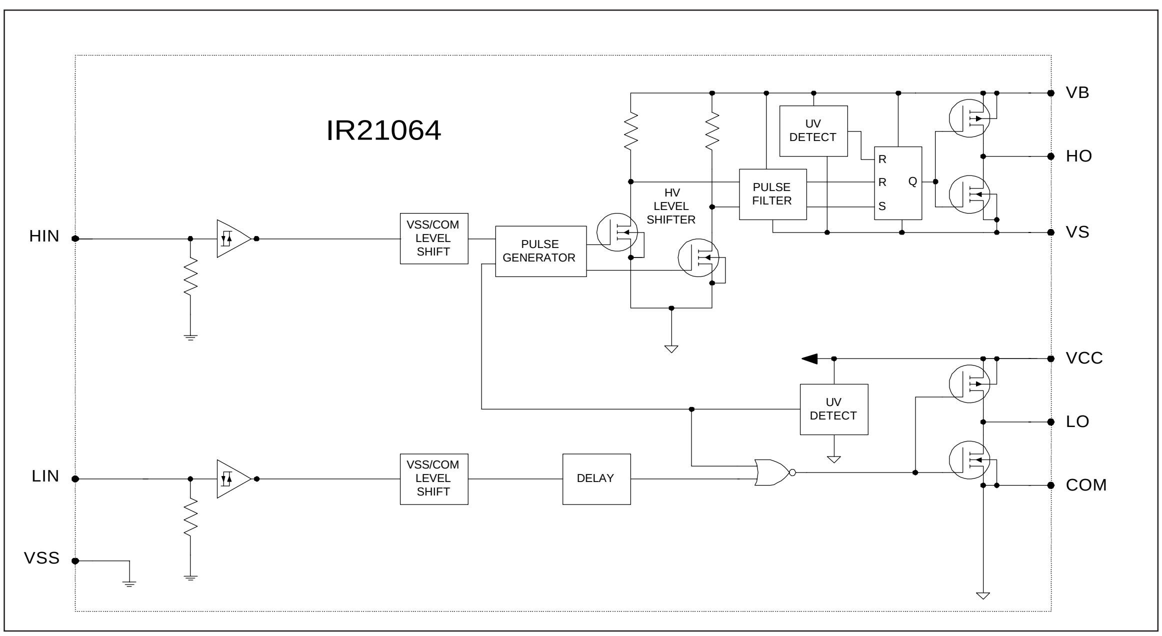
Static Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15V, V_{SS} = COM and T_A = 25°C unless otherwise specified. The V_{IL}, V_{IH} and I_{IN} parameters are referenced to V_{SS}/COM and are applicable to the respective input leads. The V_O, I_O and Ron parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V_{IH}	Logic "1" input voltage (IR2106(4))	2.9	—	—	V	V_{CC} = 10V to 20V
V_{IL}	Logic "0" input voltage (IR2106(4))	—	—	0.8		V_{CC} = 10V to 20V
V_{OH}	High level output voltage, V_{BIAS} - V_O	—	0.8	1.4		I_O = 20 mA
V_{OL}	Low level output voltage, V_O	—	0.3	0.6		I_O = 20 mA
I_{LK}	Offset supply leakage current	—	—	50	µA	V_B = V_S = 600V
I_{QBS}	Quiescent V_{BS} supply current	20	75	130		V_{IN} = 0V or 5V
I_{QCC}	Quiescent V_{CC} supply current	60	120	180		V_{IN} = 0V or 5V
I_{IN+}	Logic "1" input bias current V_{IN} = 5V (IR2106(4))	—	5	20		
I_{IN-}	Logic "0" input bias current V_{IN} = 0V (IR2106(4))	—	—	2		
V_{CCUV+} V_{BSUV+}	V_{CC} and V_{BS} supply undervoltage positive going threshold	8.0	8.9	9.8	V	
V_{CCUV-} V_{BSUV-}	V_{CC} and V_{BS} supply undervoltage negative going threshold	7.4	8.2	9.0		
V_{CCUVH} V_{BSUVH}	Hysteresis	0.3	0.7	—		
I_{O+}	Output high short circuit pulsed current	120	200	—	mA	V_O = 0V, PW ≤ 10 µs
I_{O-}	Output low short circuit pulsed current	250	350	—		V_O = 15V, PW ≤ 10 µs

Functional Block Diagrams

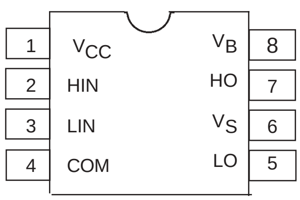




Lead Definitions

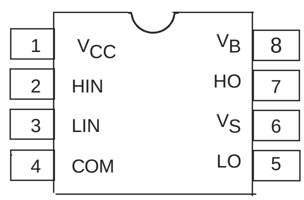
Symbol	Description
HIN	Logic input for high side gate driver output (HO), in phase
LIN	Logic input for low side gate driver output (LO), in phase
VSS	Logic Ground (IR21064 only)
V_B	High side floating supply
HO	High side gate drive output
V_S	High side floating supply return
V_{CC}	Low side and logic fixed supply
LO	Low side gate drive output
COM	Low side return

Lead Assignments



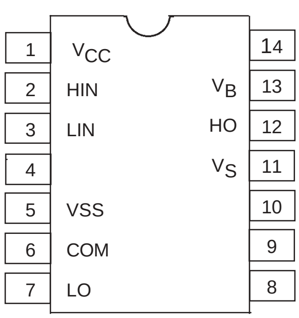
8 Lead PDIP

IR2106



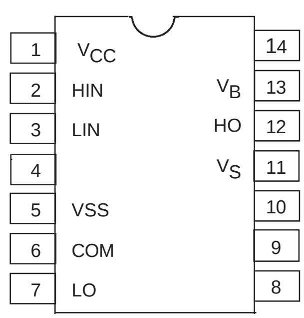
8 Lead SOIC

IR2106S



14 Lead PDIP

IR21064



14 Lead SOIC

IR21064S

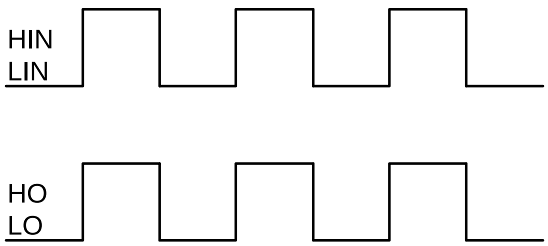


Figure 1. Input/Output Timing Diagram

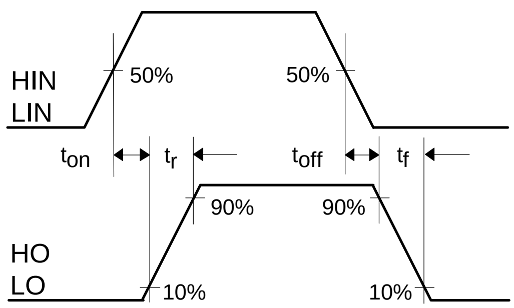


Figure 2. Switching Time Waveform Definitions

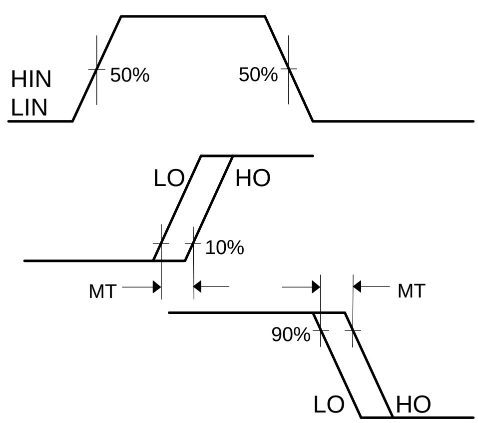


Figure 3. Delay Matching Waveform Definitions

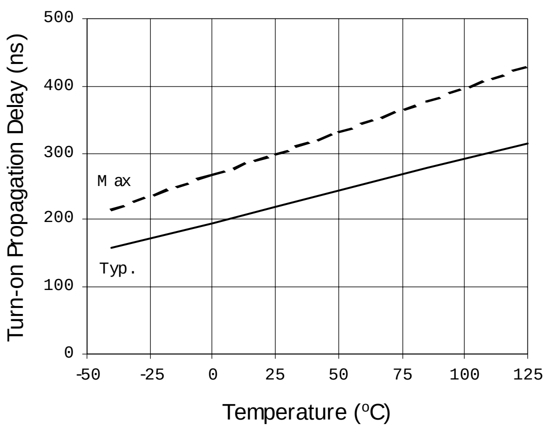


Figure 4A. Turn-on Propagation Delay vs. Temperature

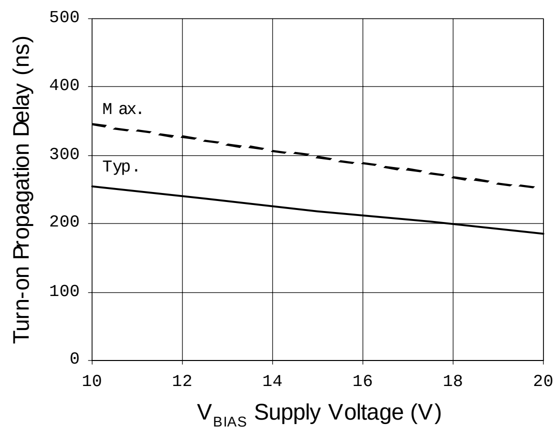


Figure 4B. Turn-on Propagation Delay vs. Supply Voltage

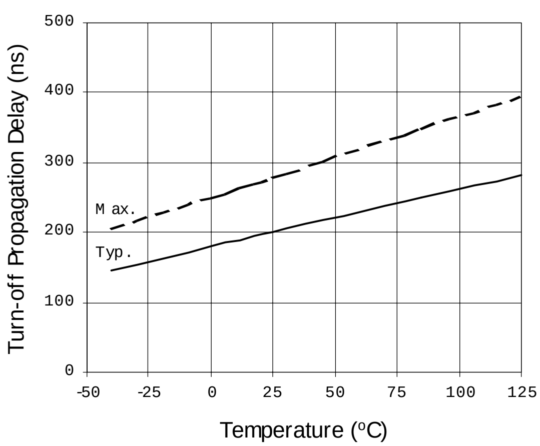


Figure 5A. Turn-off Propagation Delay vs. Temperature

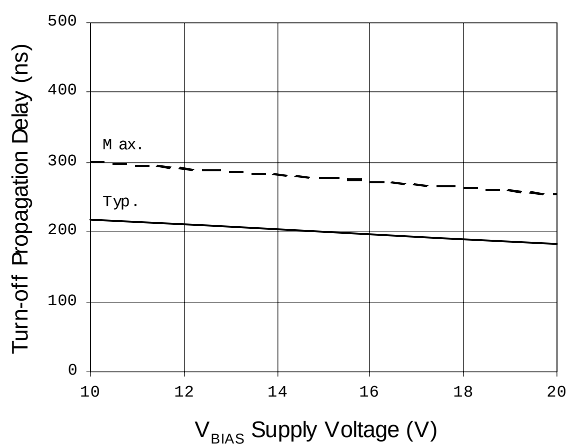


Figure 5B. Turn-off Propagation Delay vs. Supply Voltage

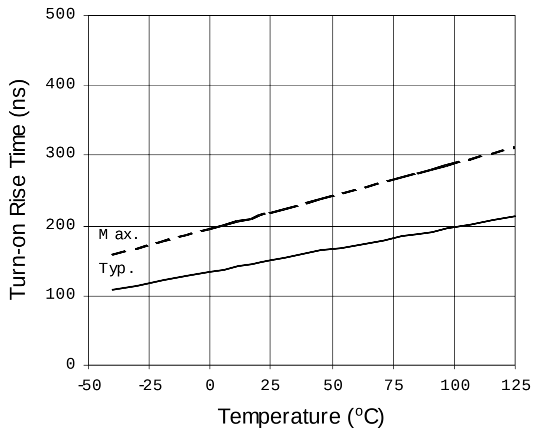


Figure 6A. Turn-on Rise Time vs. Temperature

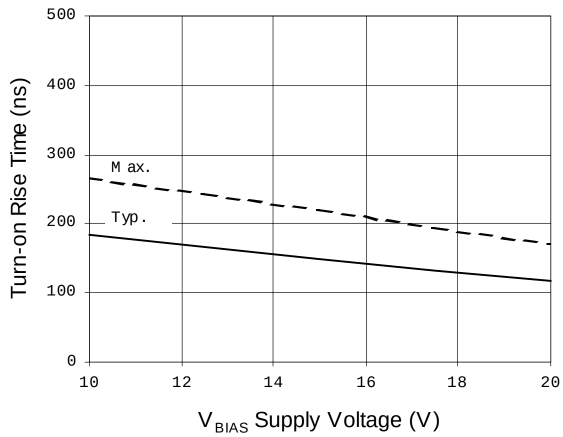


Figure 6B. Turn-on Rise Time vs. Supply Voltage

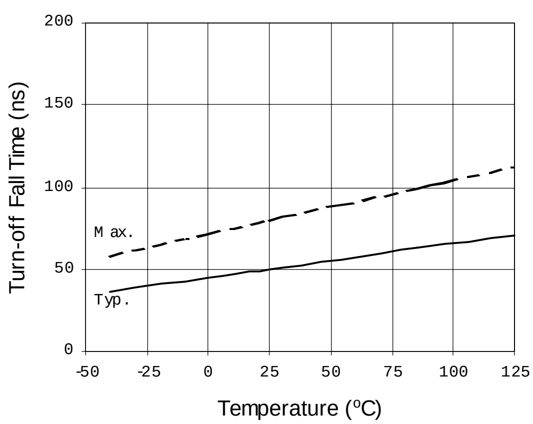


Figure 7A. Turn-off Fall Time vs. Temperature

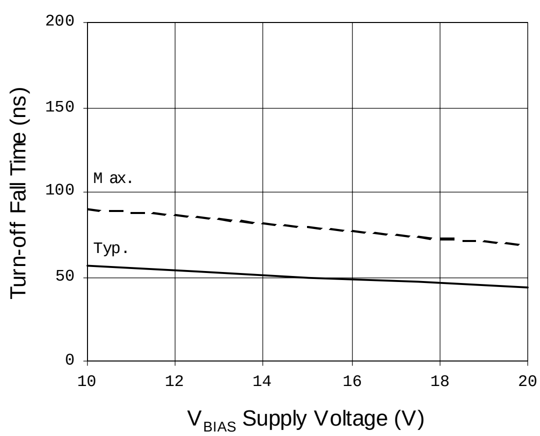


Figure 7B. Turn-off Fall Time vs. Supply Voltage

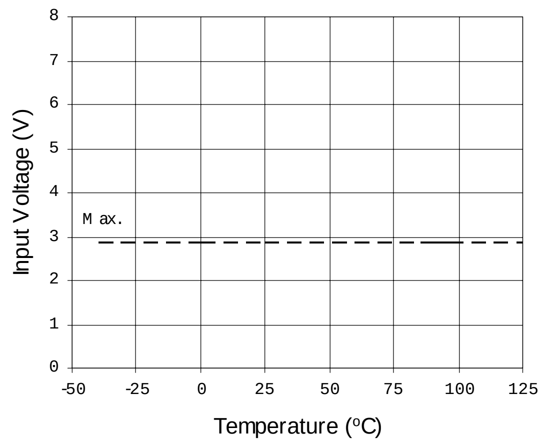


Figure 8A. Logic "1" Input Voltage vs. Temperature

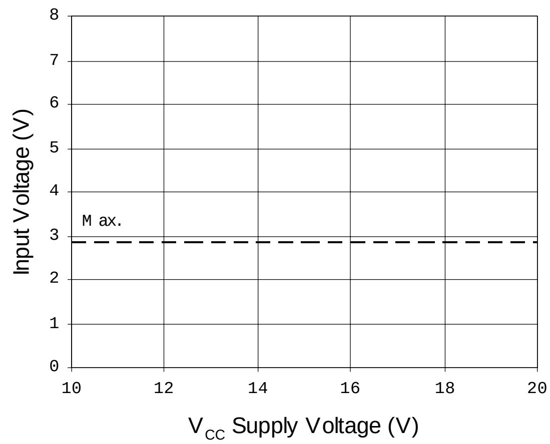


Figure 8B. Logic "1" Input Voltage vs. Supply Voltage

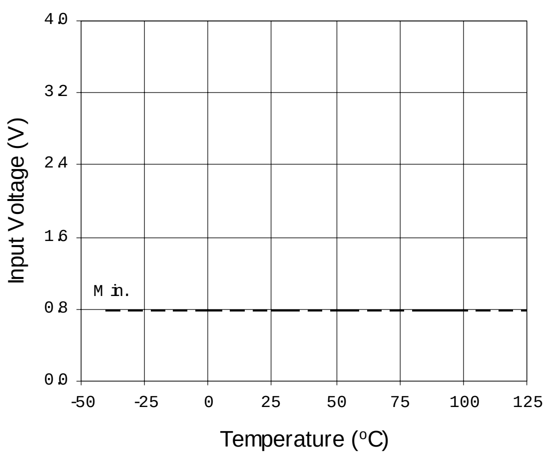


Figure 9A. Logic "0" Input Voltage vs. Temperature

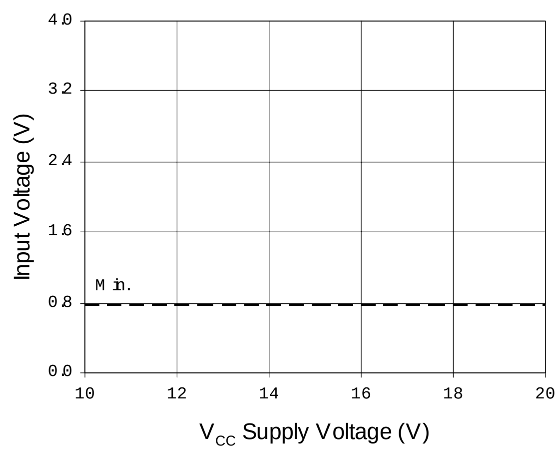


Figure 9B. Logic "0" Input Voltage vs. Supply Voltage

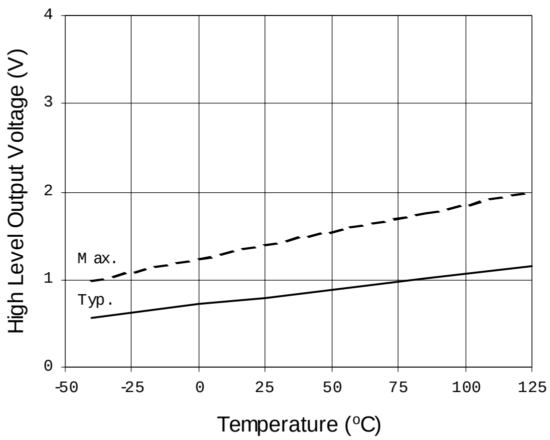


Figure 10A. High Level Output Voltage vs. Temperature

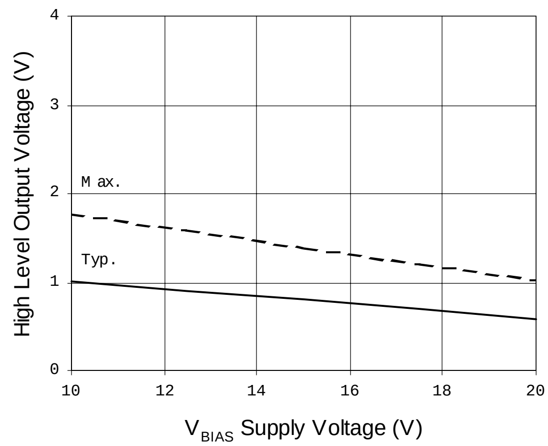


Figure 10B. High Level Output Voltage vs. Supply Voltage

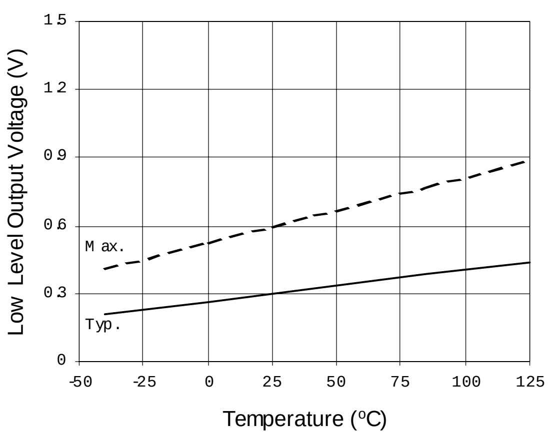


Figure 11A. Low Level Output Voltage vs. Temperature

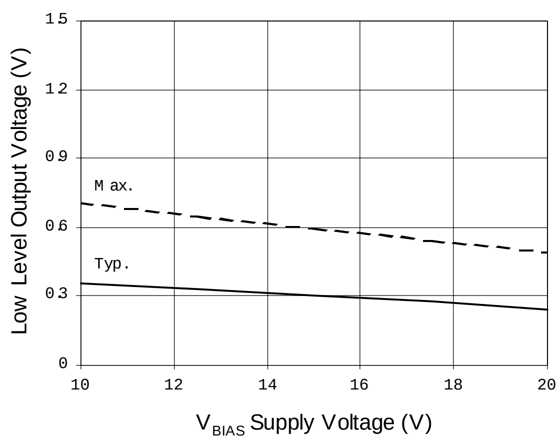


Figure 11B. Low Level Output Voltage vs. Supply Voltage

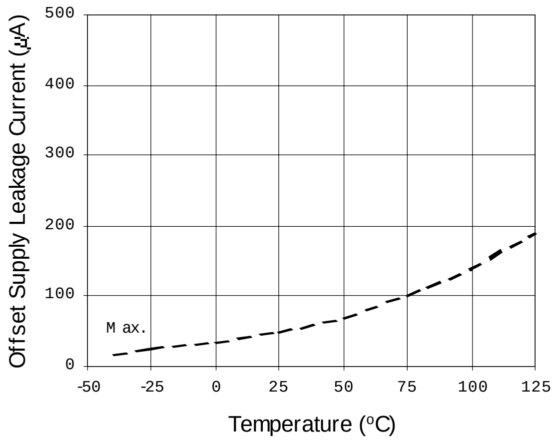


Figure 12A. Offset Supply Leakage Current vs. Temperature

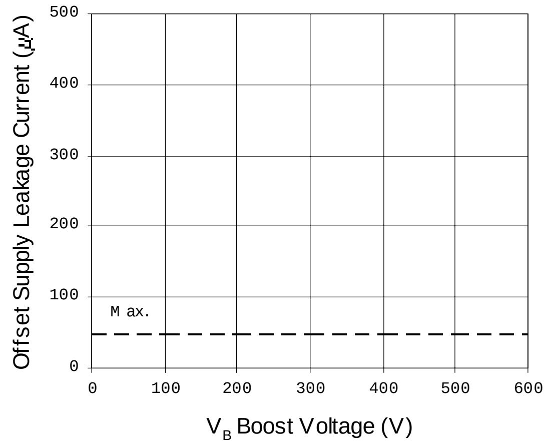


Figure 12B. Offset Supply Leakage Current vs. Supply Voltage

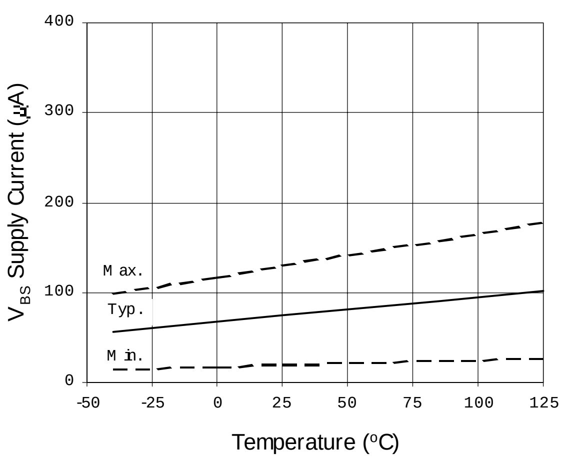


Figure 13A. V_{BS} Supply Current vs. Temperature

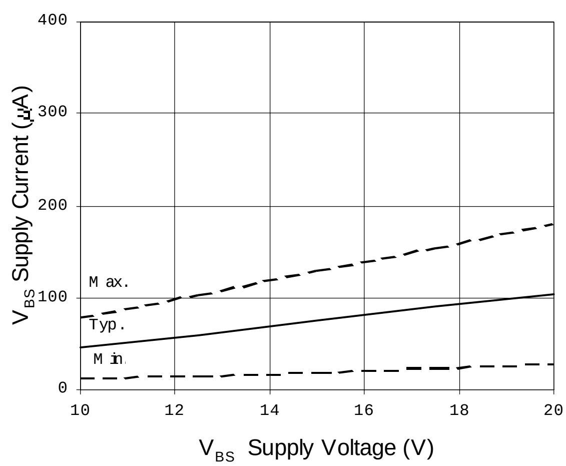


Figure 13B. V_{BS} Supply Current vs. Supply Voltage

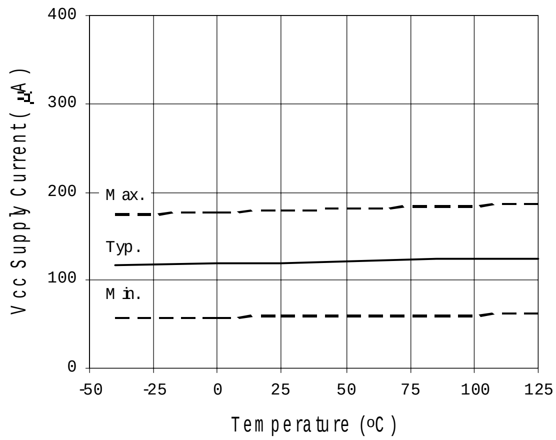


Figure 14A. Quiescent V_{CC} Supply Current vs. Temperature

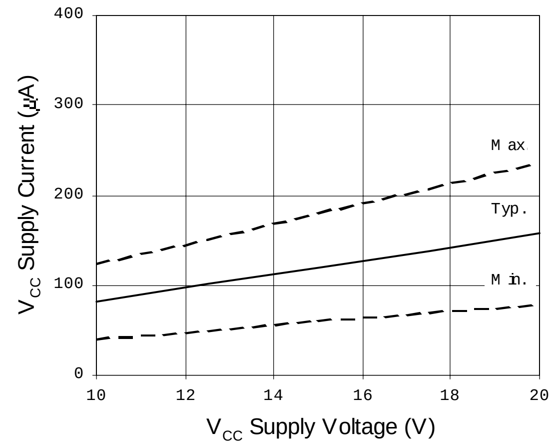


Figure 14B. Quiescent V_{CC} Supply Current vs. V_{CC} Supply Voltage

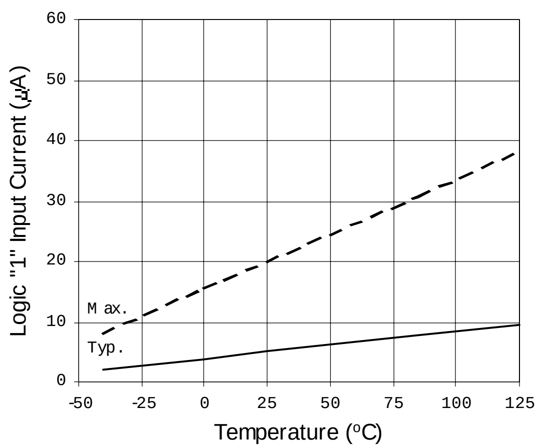


Figure 15A. Logic "1" Input Current vs. Temperature

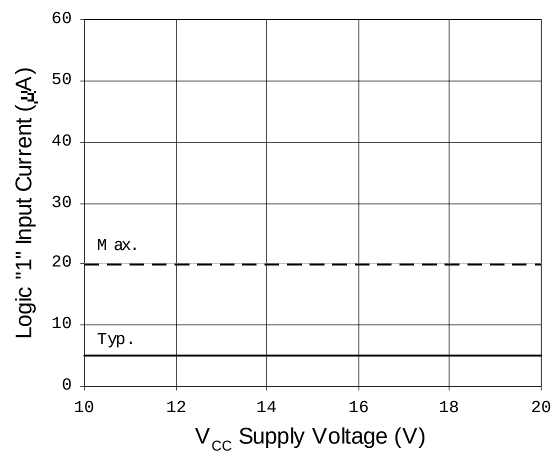


Figure 15B. Logic "1" Bias Current vs. Supply Voltage

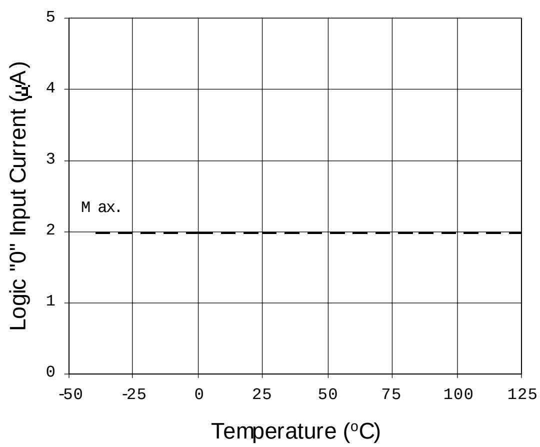


Figure 16A. Logic “0” Input Current vs. Temperature

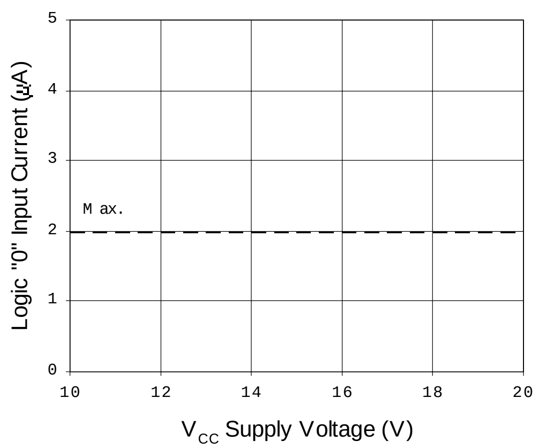


Figure 16B. Logic “0” Input Currentt vs. Supply Voltage

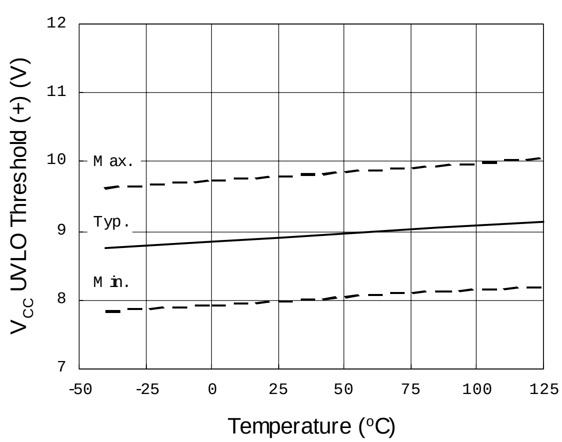


Figure 17. V_{CC} Undervoltage Threshold (+) vs. Temperature

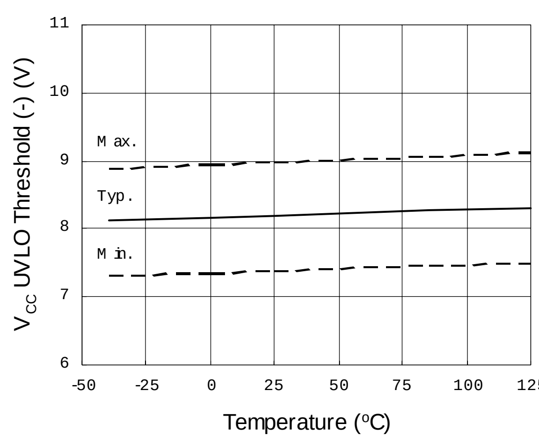


Figure 18. V_{CC} Undervoltage Threshold (-) vs. Temperature

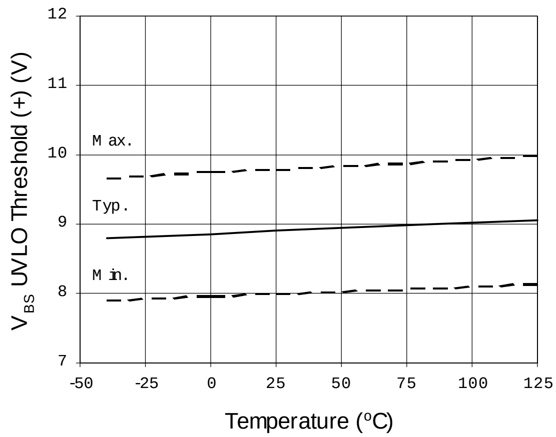


Figure 19. V_{BS} Undervoltage Threshold (+) vs. Temperature

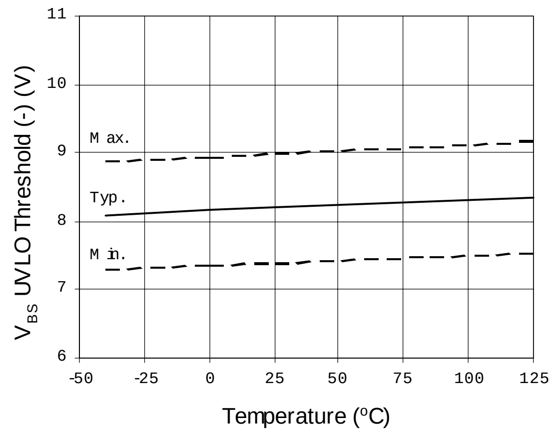


Figure 20. V_{BS} Undervoltage Threshold (-) vs. Temperature

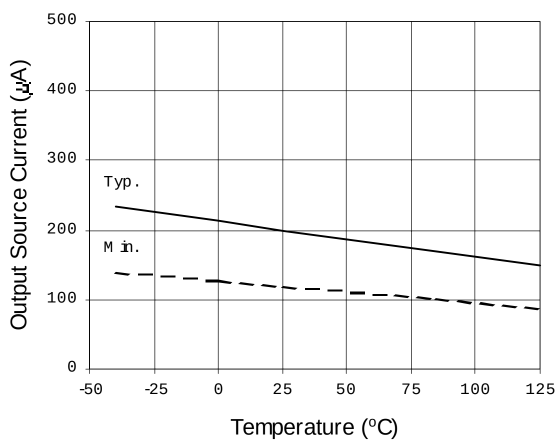


Figure 21A. Output Source Current vs. Temperature

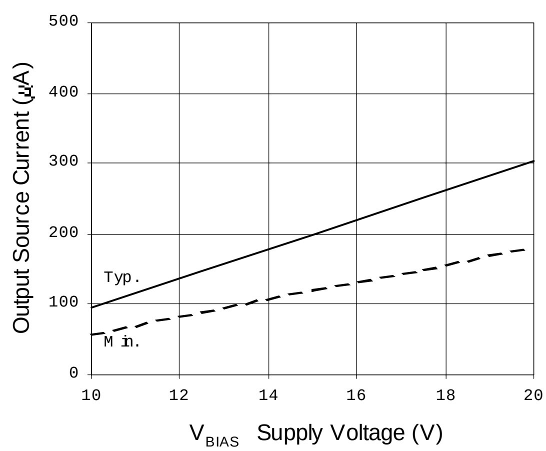


Figure 21B. Output Source Current vs. Supply Voltage

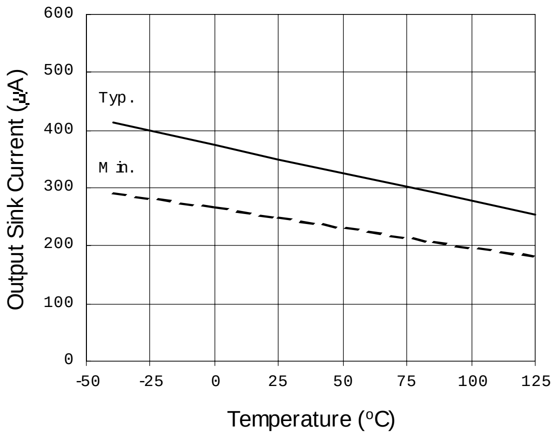


Figure 22A. Output Sink Current vs. Temperature

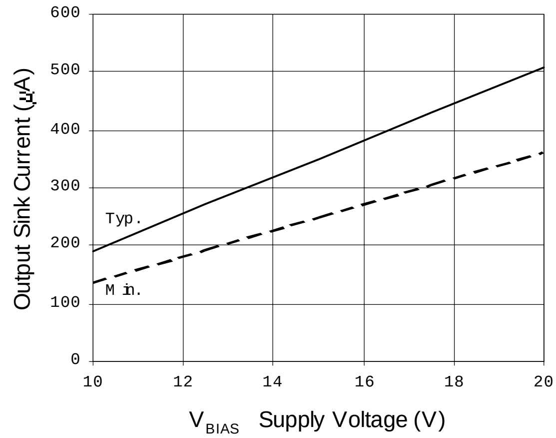


Figure 22B. Output Sink Currentt vs. Supply Voltage

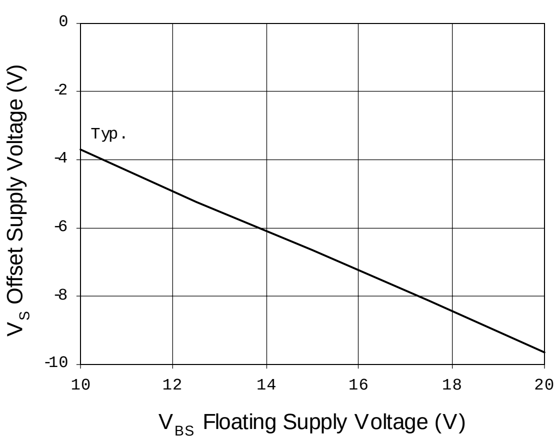


Figure 23. Maximum V_S Negative Offset vs. Supply Voltage

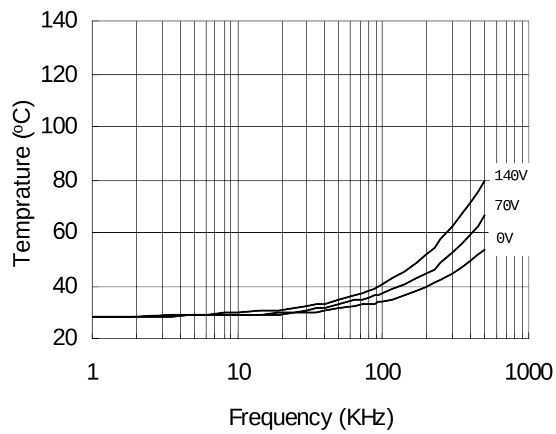


Figure 24. IR2106 vs. Frequency (IRFBC20), Rgate=33Ω, VCC=15V

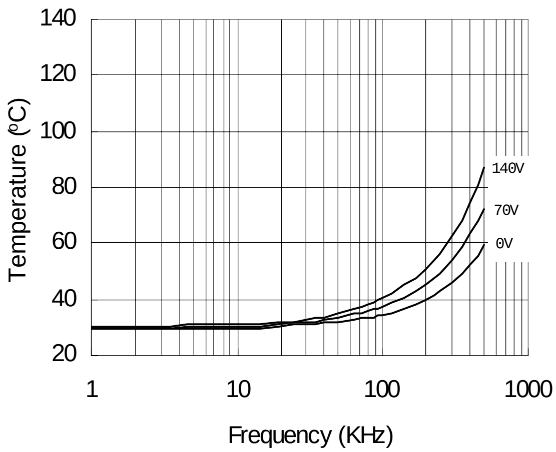


Figure 25. IR2106 vs. Frequency (IRFBC30), R_{gate}=22Ω, V_{CC}=15V

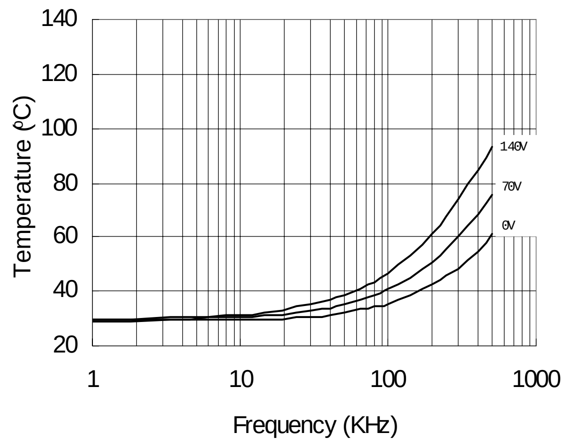


Figure 26. IR2106 vs. Frequency (IRFBC40), R_{gate}=15Ω, V_{CC}=15V

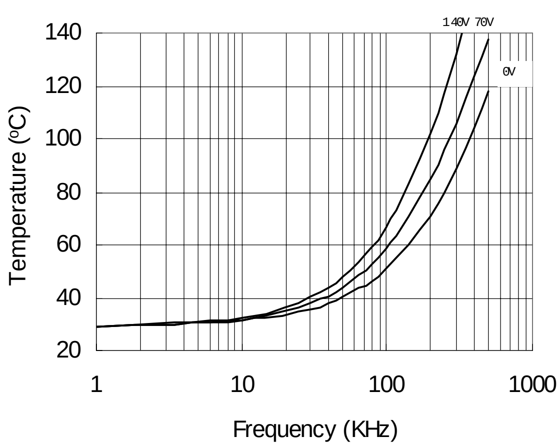


Figure 27. IR2106 vs. Frequency (IRFPE50), R_{gate}=10Ω, V_{CC}=15V

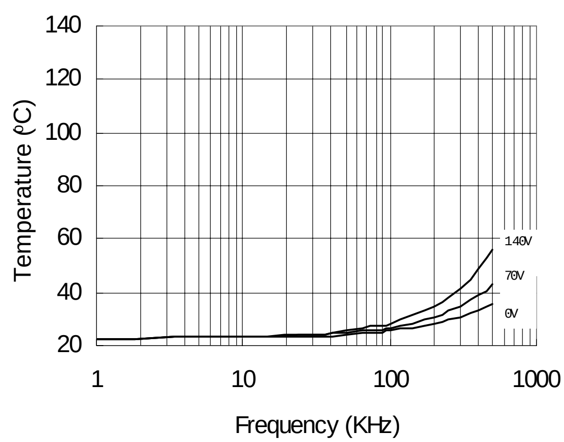


Figure 28. IR21064 vs. Frequency (IRFBC20), R_{gate}=33Ω, V_{CC}=15V

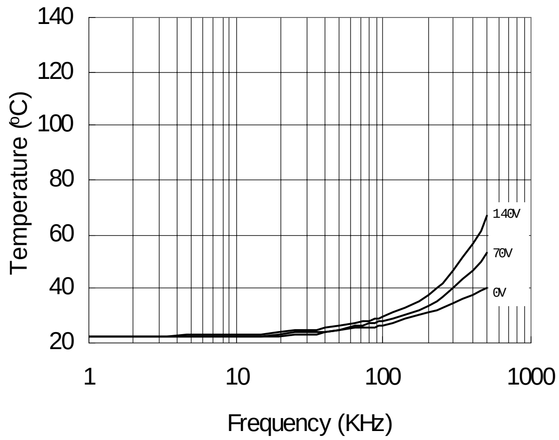


Figure 29. IR21064 vs. Frequency (IRFBC30), R_{gate}=22Ω, V_{CC}=15V

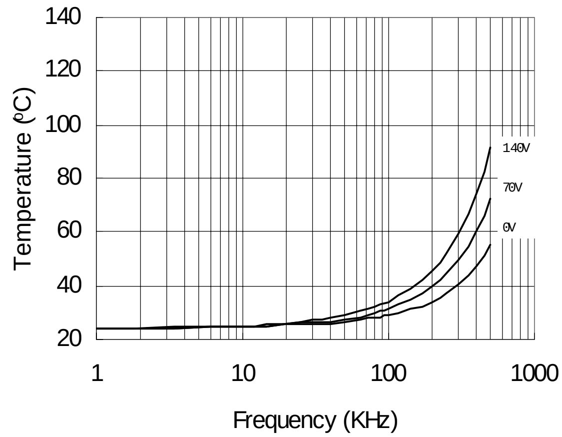


Figure 30. IR21064 vs. Frequency (IRFBC40), R_{gate}=15Ω, V_{CC}=15V

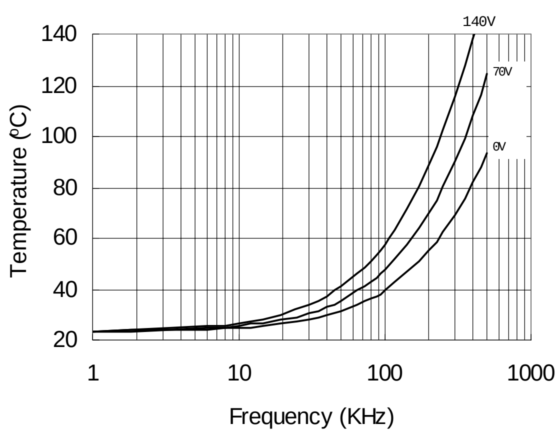


Figure 31. IR21064 vs. Frequency (IRFPE50), R_{gate}=10Ω, V_{CC}=15V

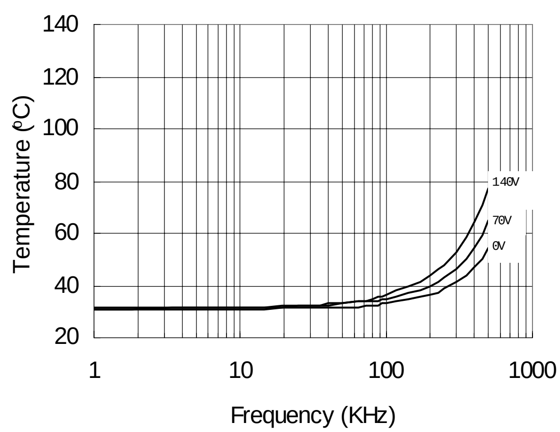


Figure 32. IR2106S vs. Frequency (IRFBC20), R_{gate}=33Ω, V_{CC}=15V

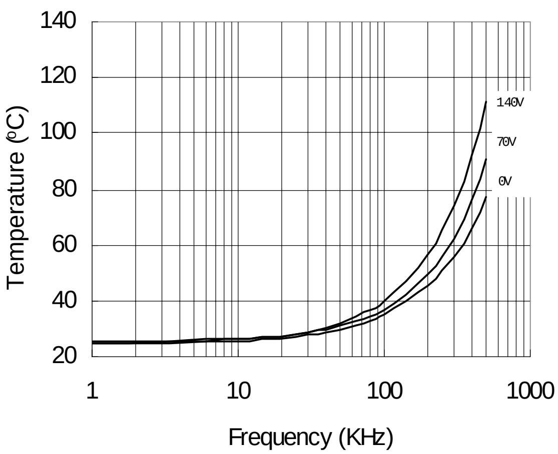


Figure 33. IR2106S vs. Frequency (IRFBC30), R_{gate}=22Ω, V_{CC}=15V

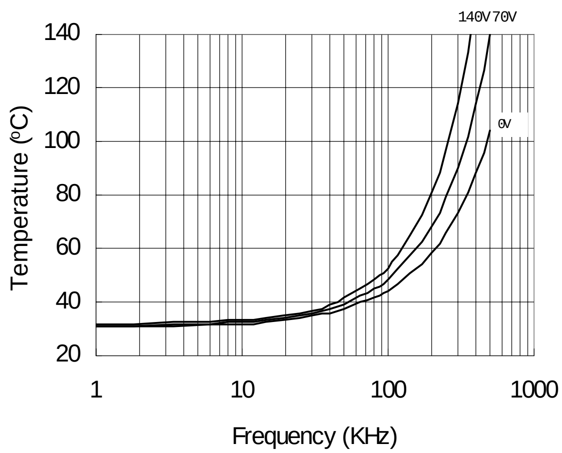


Figure 34. IR2106S vs. Frequency (IRFBC40), R_{gate}=15Ω, V_{CC}=15V

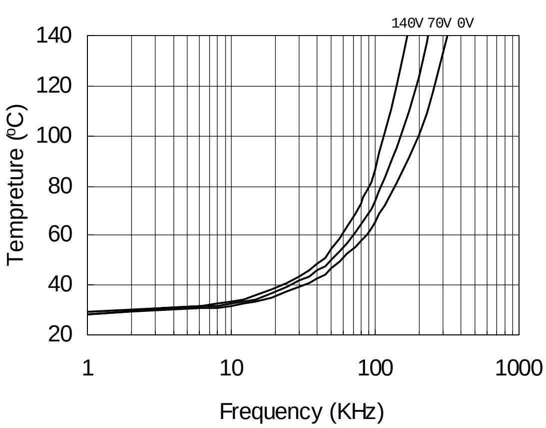


Figure 35. IR2106S vs. Frequency (IRFPE50), R_{gate}=10Ω, V_{CC}=15V

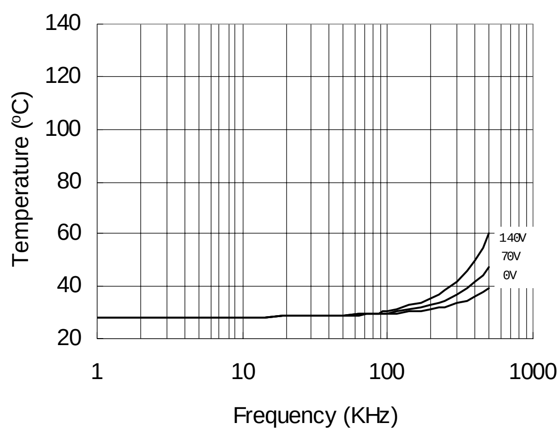


Figure 36. IR21064S vs. Frequency (IRFBC20), R_{gate}=33Ω, V_{CC}=15V

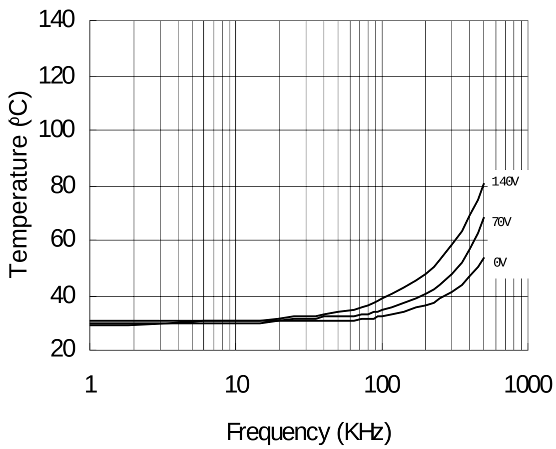


Figure 37. IR21064S vs. Frequency (IRFBC30), R_{gate}=22Ω, V_{CC}=15V

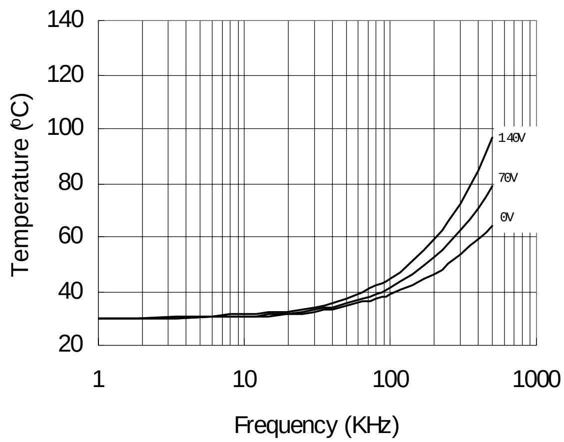


Figure 38. IR21064S vs. Frequency (IRFBC40), R_{gate}=15Ω, V_{CC}=15V

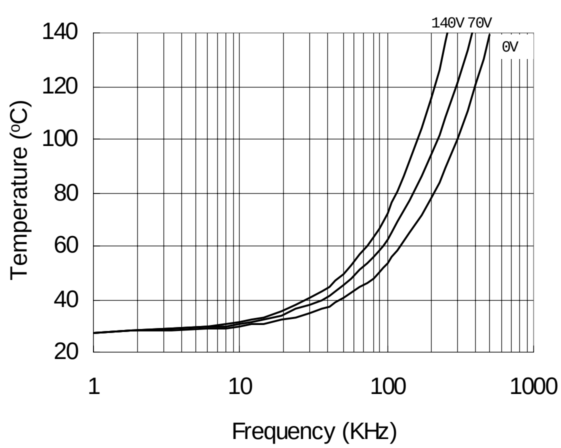
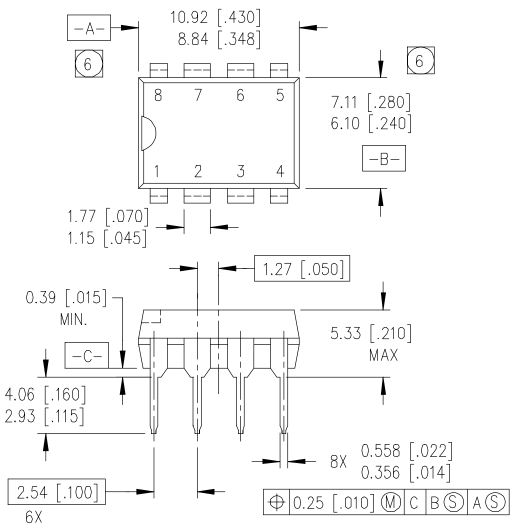
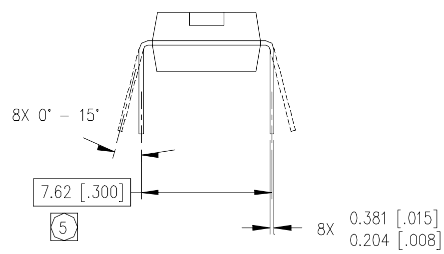


Figure 39. IR21064S vs. Frequency (IRFPE50), R_{gate}=10Ω, V_{CC}=15V

Case Outlines

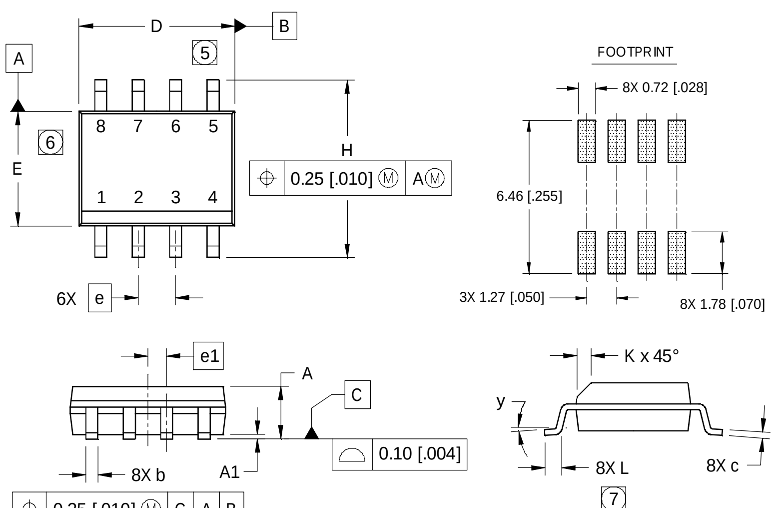


NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-001AB.
5. MEASURED WITH THE LEADS CONSTRAINED TO BE PERPENDICULAR TO DATUM PLANE C.
6. DIMENSION DOES NOT INCLUDE MOLD PROTUSIONS. MOLD PROTUSIONS SHALL NOT EXCEED 0.25 [.010].



01-6014
01-3003 01 (MS-001AB)

8 Lead PDIP

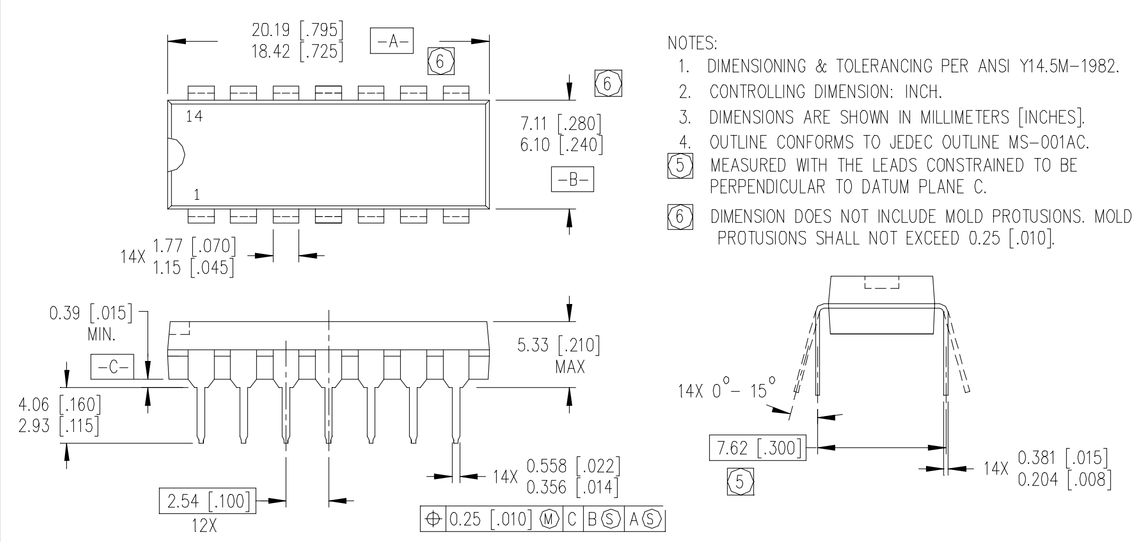


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

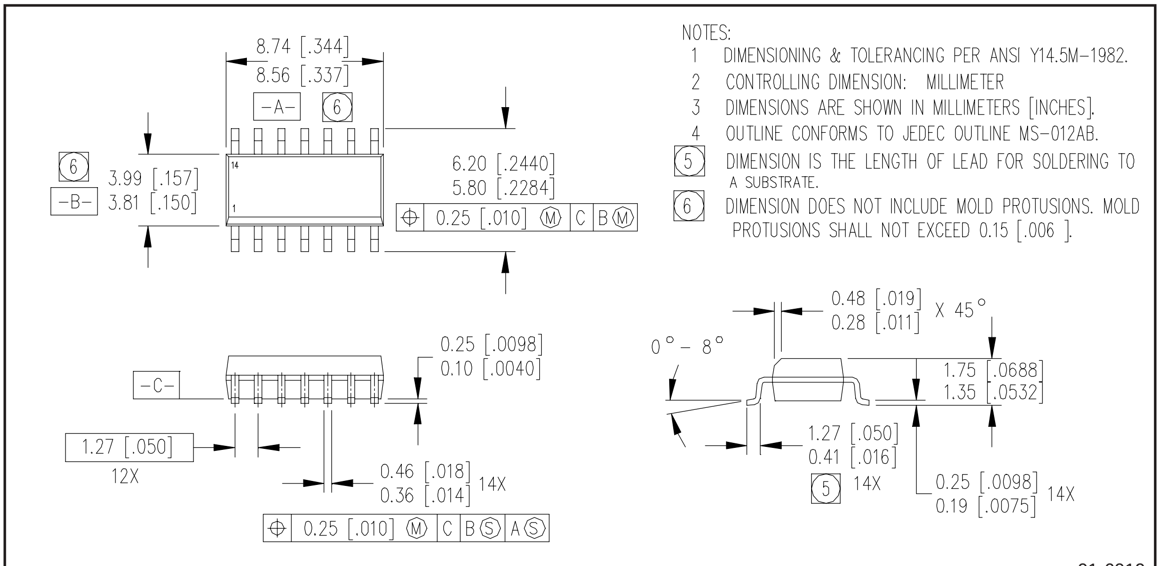
01-6027
01-0021 11 (MS-012AA)

8 Lead SOIC



14 Lead PDIP

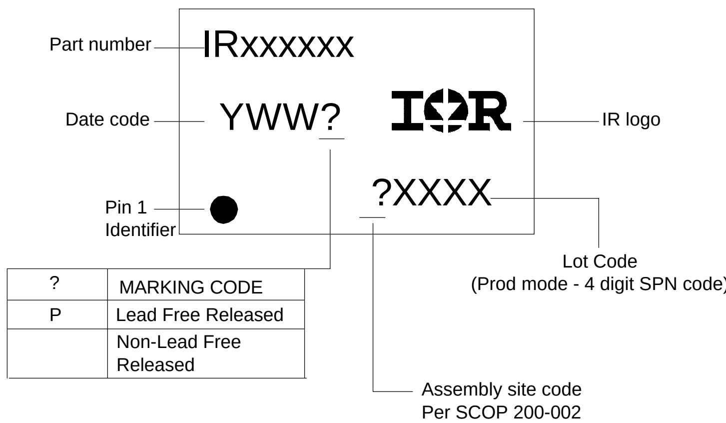
01-6010
01-3002 03 (MS-001AC)



14 Lead SOIC (narrow body)

01-6019
01-3063 00 (MS-012AB)

LEADFREE PART MARKING INFORMATION



ORDER INFORMATION

Basic Part (Non-Lead Free)
8-Lead PDIP IR2106 order IR2106
8-Lead SOIC IR2106S order IR2106S
14-Lead PDIP IR21064 order IR21064
14-Lead SOIC IR21064S order IR21064S

Leadfree Part
8-Lead PDIP IR2106 order IR2106PbF
8-Lead SOIC IR2106S order IR2106SPbF
14-Lead PDIP IR21064 order IR21064PbF
14-Lead SOIC IR21064S order IR21064SPbF

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Data and specifications subject to change without notice. 4/12/2004

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Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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